Norbert Esser

List of Publications by Year
in descending order

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241	5,068	76326	161849
papers	citations	40	54
		h-index	g-index

251	251	251	3818
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Surface Resonant Raman Scattering from Cu(110). Physical Review Letters, 2022, 128, .	7.8	1
2	Determination of residual dimethyl sulfoxide by high-resolution continuum source graphite furnace molecular absorption spectrometry. Spectrochimica Acta, Part B: Atomic Spectroscopy, 2021, 177, 106050.	2.9	1
3	Surface localized phonon modes at the Si(553)-Au nanowire system. Physical Review B, 2021, 103, .	3.2	6
4	Controlled growth of ordered monolayers of N-heterocyclic carbenes on silicon. Nature Chemistry, 2021, 13, 828-835.	13.6	34
5	Spectroscopic Analysis of Rare-Earth Silicide Structures on the Si(111) Surface. Materials, 2021, 14, 4104.	2.9	3
6	Adsorption of tolueneâ€3,4â€dithiol on silver islands investigated by surfaceâ€enhanced Raman spectroscopy. Journal of Raman Spectroscopy, 2020, 51, 788-794.	2.5	7
7	Vibrational Raman spectroscopy on adsorbate-induced low-dimensional surface structures. Surface Science Reports, 2020, 75, 100480.	7.2	4
8	Vibration-Driven Self-Doping of Dangling-Bond Wires on Si(553)-Au Surfaces. Physical Review Letters, 2020, 124, 146802.	7.8	15
9	Gradient metal nanoislands as a unified surface enhanced Raman scattering and surface enhanced infrared absorption platform for analytics. Analyst, The, 2019, 144, 5271-5276.	3.5	16
10	Organic Molecule Adsorption on Stepped Siâ€“Au Surfaces: Role of Functional Group on Geometry and Electronic Structure. Physica Status Solidi (B): Basic Research, 2019, 256, 1800653.	1.5	1
11	Raman Spectroscopy on Surface Phonons of Si(hhk) Surfaces Modified by Au Submonolayers. Physica Status Solidi (B): Basic Research, 2019, 256, 1800341.	1.5	4
12	Electric Field Induced Raman Scattering at the Sbâ€“InP(110) Interface: The Surface Dipole Contribution. Physica Status Solidi (B): Basic Research, 2019, 256, 1800314.	1.5	3
13	Controlling the Local Electronic Properties of Si(553)-Au through Hydrogen Doping. Physical Review Letters, 2018, 120, 166801.	7.8	12
14	Electronic Properties of Ag Reconstructions on Si(111): Coulomb Blockade Behavior at Room Temperature. Physica Status Solidi (B): Basic Research, 2018, 255, 1700494.	1.5	2
15	A new concept of efficient therapeutic drug monitoring using the high-resolution continuum source absorption spectrometry and the surface enhanced Raman spectroscopy. Spectrochimica Acta, Part B: Atomic Spectroscopy, 2018, 142, 91-96.	2.9	15
16	Selective adsorption of toluene-3,4-dithiol on Si(553)-Au surfaces. Physical Review B, 2018, 97, .	3.2	8
17	Vibrational properties of the Au-(<mml:math) Tj ETQq1 1 0.784314 rgBT /Overlock 10 Tf 50 107 Td (xmlns:mml="http://www.w3.org/1	3.2	10
18	Surface vibrations in the <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:msub><mml:mi mathvariant="normal">T</mml:mi><mml:mn>4</mml:mn></mml:msub></mml:math> and <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:msub><mml:mi mathvariant="normal">H</mml:mi><mml:mn>3</mml:mn></mml:msub></mml:math> Pb phases on Si(111). Physical Review B, 2018, 98, .	3.2	4

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19	Optical properties of In₂O₃ from experiment and first-principles theory: influence of lattice screening. New Journal of Physics, 2018, 20, 053016.	2.9	20
20	Influence of anisotropic Si(111)-(4â€‰Ã—â€‰1)-In surface on growth of nanoscale In islands. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2018, 36, 04H103.	1.2	1
21	Introduction to Raman scattering at surfaces. , 2018, , 549-551.		1
22	An in situ XPS study of L-cysteine co-adsorbed with water on polycrystalline copper and gold. Applied Surface Science, 2018, 435, 870-879.	6.1	19
23	Ordinary dielectric function of corundumlike <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mi>Î±</mml:mi><mml:mtext>â^'</mml:mtext><mml:msub mathvariant="normal">O</mml:mi><mml:mn>3</mml:mn></mml:msub></mml:mrow></mml:math> from 40ÂmeV to 20 eV. Physical Review Materials, 2018, 2, .	2.4	25
24	Metal surfaces: Si nanoribbons on Ag(110). , 2018, , 599-600.		0
25	Au-terminated Si(553). , 2018, , 597-598.		0
26	Clean Si(111). , 2018, , 569-571.		0
27	Sb monolayer-terminated IIIâ€“V(110) surfaces. , 2018, , 572-579.		0
28	Clean Ge(001). , 2018, , 564-568.		0
29	Au-terminated Si(111). , 2018, , 594-596.		0
30	Fundamentals of surface Raman spectroscopy. , 2018, , 552-554.		0
31	Clean InP(110). , 2018, , 560-563.		0
32	As-terminated Si(111). , 2018, , 585-587.		0
33	Sb-terminated Si(001) and Ge(001). , 2018, , 580-584.		0
34	Surface resonance. , 2018, , 557-558.		0
35	Localized Synthesis of Conductive Copperâ€“Tetracyanoquinodimethane Nanostructures in Ultrasmall Microchambers for Nanoelectronics. ACS Applied Materials & Interfaces, 2017, 9, 17271-17278.	8.0	6
36	Characterization of anisotropically shaped silver nanoparticle arrays via spectroscopic ellipsometry supported by numerical optical modeling. Applied Surface Science, 2017, 421, 460-464.	6.1	11

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37	Optical anisotropy of quasi-1D rare-earth silicide nanostructures on Si(001). Applied Surface Science, 2017, 399, 648-653.	6.1	5
38	Bi-Axial Growth Mode of Auâ€“TTF Nanowires Induced by Tilted Molecular Column Stacking. Journal of Physical Chemistry C, 2017, 121, 23200-23206.	3.1	2
39	Si(775)-Au atomic chains: Geometry, optical properties, and spin order. Physical Review Materials, 2017, 1, .	2.4	17
40	Inversion of absorption anisotropy and bowing of crystal field splitting in wurtzite MgZnO. Applied Physics Letters, 2016, 108, .	3.3	11
41	Surface vibrational Raman modes of In:Si(111)(4Ã—1)and(8Ã—2)nanowires. Physical Review B, 2016, 94, .	3.2	18
42	Conductive single nanowires formed and analysed on microfluidic devices. Journal of Materials Chemistry C, 2016, 4, 9235-9244.	5.5	13
43	Grand canonical Peierls transition in In/Si(111). Physical Review B, 2016, 93, .	3.2	23
44	Vibration eigenmodes of the Au- <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mo>(</mml:mo><mml:mn>5</mml:mn><mml:mo>Ã—</mml /Si(111) surface studied by Raman spectroscopy and first-principles calculations. Physical Review B, 2016, 94, .	3.2	16
45	Polarization- and Wavelength-Dependent Surface-Enhanced Raman Spectroscopy Using Optically Anisotropic Rippled Substrates for Sensing. ACS Sensors, 2016, 1, 318-323.	7.8	36
46	Preparation and structure of ultra-thin GaN (0001) layers on In0.11Ga0.89N-single quantum wells. Materials Science in Semiconductor Processing, 2016, 55, 7-11.	4.0	12
47	Near valence-band electronic properties of semiconducting<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mi>Î²</mml:mi><mml:msub><mml:mrow><mml:mo>â^’</mml mathvariant="normal">O</mml:mi><mml:mn>3</mml:mn></mml:msub></mml:mrow></mml:math>(100) single crystals. Physical Review B, 2015, 92, .	3.2	47
48	Vibrational Raman scattering from surfaces of III-V semiconductors: Microscopic and macroscopic surface modes. Physica Status Solidi (B): Basic Research, 2015, 252, 11-18.	1.5	4
49	GaN<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mi>m</mml:mi></mml:math>-plane: Atomic structure, surface bands, and optical response. Physical Review B, 2015, 91, .	3.2	52
50	Spectrometer system using a modular echelle spectrograph and a laser-driven continuum source for simultaneous multi-element determination by graphite furnace absorption spectrometry. Spectrochimica Acta, Part B: Atomic Spectroscopy, 2015, 107, 11-16.	2.9	14
51	Surface properties of annealed semiconducting Î²-Ga2O3 (1 0 0) single crystals for epitaxy. Applied Surface Science, 2015, 349, 368-373.	6.1	46
52	Label-free biosensors based on in situ formed and functionalized microwires in microfluidic devices. Analyst, The, 2015, 140, 7896-7901.	3.5	22
53	Metal-to-Insulator Transition in Au Chains on Si(111)-5Ã—2-Au by Band Filling: Infrared Plasmonic Signal and Ab Initio Band Structure Calculation. Journal of Physical Chemistry Letters, 2015, 6, 3615-3620.	4.6	13
54	Optical properties of magnesium doped AlxGa1â^'xN (0.61 â‰¤ x â‰¤ 0.73). Journal of Applied Physics, 2014, 116, 143103.	2.5	7

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55	Raman spectroscopy study of silicon nanoribbons on Ag(110). Applied Physics Letters, 2014, 104, 161612.	3.3	14
56	Confirmation of intrinsic electron gap states at nonpolar GaN(1-100) surfaces combining photoelectron and surface optical spectroscopy. Applied Physics Letters, 2014, 104, .	3.3	28
57	A synchrotron-radiation-based variable angle ellipsometer for the visible to vacuum ultraviolet spectral range. Review of Scientific Instruments, 2014, 85, 055117.	1.3	15
58	Surface phonons of the Si(111)-(<mml:math) Tj ETQq0 0 0 rgBT /Overlock 10 Tf 50 627 Td (xmlns:mml="http://www.w3.org/1998/Math reconstruction observed by Raman spectroscopy. Physical Review B, 2014, 89, .	3.2	26
59	Reflectance difference spectroscopy of water on Cu(110). Surface Science, 2014, 627, 16-22.	1.9	4
60	Band gap renormalization and Burstein-Moss effect in silicon- and germanium-doped wurtzite GaN up to<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:msup><mml:mrow><mml:mn>10</mml:mn></mml:mrow><mml:mn>20</ mathvariant="normal">cm</mml:mi><mml:msup><mml:mrow /><mml:mrow><mml:mo>â^'</mml:mo><mml:mn>3</mml:mn></mml:mrow></mml:msup></mml:math>. Physical Review B, 2014, 90, .	3.2	133
61	Temperature dependent dielectric function and reflectivity spectra of nonpolar wurtzite AlN. Thin Solid Films, 2014, 571, 502-505.	1.8	7
62	DNA Structures on Silicon and Diamond. Springer Series in Surface Sciences, 2014, , 47-59.	0.3	4
63	Ultraviolet vacuum ultraviolet optical functions for SrTiO3 and NdGaO3 crystals determined by spectroscopic ellipsometry. Journal of Applied Physics, 2013, 114, 043513.	2.5	4
64	Specific features of Yb3+ ions in electronic band energy structure and optical functions of RbNd(WO4)2 crystals: Synchrotron ellipsometry measurements and DFT simulations. Journal of Alloys and Compounds, 2013, 577, 237-246.	5.5	0
65	Transition energies and direct/indirect band gap crossing in zinc-blende Al<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mrow /><mml:mi>x</mml:mi></mml:msub></mml:math>Ga<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mrow /><mml:mrow><mml:mn>1</mml:mn><mml:mo>â^'</mml:mo><mml:mi>x</mml:mi></mml:mrow></mml:msub></mml:math>N.	3.2	39
66	Anisotropic absorption and emission of bulk<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:mo>(</mml:mo><mml:mn>1</mml:mn><mml:mover) Tj ETQq0 0 0 rgBT /Overlock 10 Tf 50 297 Td Physical Review B, 2013, 87, .	3.2	61
67	Structural phase transitions in ferroelectric crystals and thin films studied by VUV spectroscopic ellipsometry with synchrotron radiation. Phase Transitions, 2013, 86, 932-940.	1.3	2
68	Spectral ellipsometry study in the range of electronic excitations and band structure of [(CH3)2CHNH3]4Cd3Cl10 crystals. Materials Chemistry and Physics, 2013, 139, 770-774.	4.0	2
69	STM analysis of defects at the GaAs(001)-c(4Ã—4) surface. Surface Science, 2013, 617, 162-166.	1.9	3
70	Negative spin-exchange splitting in the exciton fine structure of AlN. Applied Physics Letters, 2013, 102, .	3.3	18
71	Aging-induced optical anisotropy in thermally grown thin ZnTPP films on Si. Physica Status Solidi (B): Basic Research, 2013, 250, 1791-1794.	1.5	1
72	Pyrrole adsorption on GaAs(001)-<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mi>c</mml:mi></mml:math>(4<mml:math) Tj ETQq0 0 0 rgBT /Overlock 10 Tf 50 67 Td (xmlns:mml="http://www 2012, 85, .	3.2	5

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73	phonons of Ge(001) and their correlation with the<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mi>p</mml:mi></mml:math>(2<mml:math) Tj ETQq1 1 0.784314 rgBT /Overlock 10 Tf 50 747 Td (xmlns:mml="http://www.w3.org/1998/Math/MathML" and<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mi>c</mml:mi></mml:m	3.2	14
74	Optical properties of cubic GaN from 1 to 20 eV. Physical Review B, 2012, 85, .	3.2	55
75	Preparation and atomic structure of reconstructed (0001) InGaN surfaces. Journal of Applied Physics, 2012, 112, 033509.	2.5	5
76	Electronic and Optical Properties of Strontium Barium Niobate Single Crystals. Ferroelectrics, 2012, 426, 194-205.	0.6	14
77	Electronic Properties of KDP and DKDP Crystals:Ab-InitioCalculations and Spectral Ellipsometry Experiment. Ferroelectrics, 2011, 417, 20-24.	0.6	4
78	Influence of exciton-phonon coupling and strain on the anisotropic optical response of wurtzite AlN around the band edge. Physical Review B, 2011, 83, .	3.2	46
79	Spectral Ellipsometry Study of SBN Single Crystals in Visible and Ultraviolet Region. Ferroelectrics, 2011, 417, 14-19.	0.6	6
80	Adsorbate-induced modification of the surface electronic structure at GaAs(001) surfaces. Physical Review B, 2011, 83, .	3.2	8
81	In-situ optical spectroscopy and electronic properties of pyrrole sub-monolayers on Ga-rich GaAs(001). Journal of Nanoparticle Research, 2011, 13, 5847-5853.	1.9	3
82	Reconstruction dependent growth of lead phthalocyanine layers on GaAs<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:mo>(</mml:mo><mml:mn>001</mml:mn><mml:mo>)</mml:mo></mml:mrow></mml:math>surfac Physical Review B, 2011, 84, .	3.2	3
83	Optical properties of MgZnO alloys: Excitons and exciton-phonon complexes. Journal of Applied Physics, 2011, 110, .	2.5	50
84	Synchrotron-based photoluminescence excitation spectroscopy applied to investigate the valence band splittings in AlN and Al0.94Ga0.06N. Applied Physics Letters, 2011, 99, 021903.	3.3	7
85	Detection of Yb impurities in the VUV spectral range of NdGaO3 crystals. Optics Communications, 2010, 283, 3998-4003.	2.1	3
86	MBE growth of cubic AlN on 3Câ€“SiC substrate. Physica Status Solidi (A) Applications and Materials Science, 2010, 207, 1365-1368.	1.8	10
87	Valence-band splitting and optical anisotropy of AlN. Physica Status Solidi (B): Basic Research, 2010, 247, 1679-1682.	1.5	26
88	Synchrotron infrared spectroscopic ellipsometry for characterization of biofunctional surfaces. Physica Status Solidi (B): Basic Research, 2010, 247, 1925-1931.	1.5	10
89	Adsorbateâ€induced modification of the surface electric field of GaAs (001)â€c(4â€‰Ã—â€‰4) measured via the linear electroâ€optic effect. Physica Status Solidi (B): Basic Research, 2010, 247, 1941-1945.	1.5	6
90	Metalâ€“insulator transition in Si(111)â€(4â€‰Ã—â€‰1)/(8â€‰Ã—â€‰2)â€In studied by optical spectroscopy. Physica Status Solidi (B): Basic Research, 2010, 247, 2033-2039.	1.5	11

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91	Inâ€situ IR synchrotron mapping ellipsometry on stimuliâ€responsive PAAâ€bâ€PS/PEG mixed polymer brushes. Physica Status Solidi C: Current Topics in Solid State Physics, 2010, 7, 197-199.	0.8	18
92	Electronic excitations in B12As2and their temperature dependence by vacuum ultraviolet ellipsometry. Journal of Physics Condensed Matter, 2010, 22, 395801.	1.8	4
93	Optical spectra of ZnO in the far ultraviolet: First-principles calculations and ellipsometric measurements. Physical Review B, 2010, 81, .	3.2	48
94	Energy band structure and optical response function of icosahedral<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mtext>B</mml:mtext><mml:mrow><mml:mn>12</mml:mn></mml:mrow></mml:msu A spectroscopic ellipsometry and first-principles calculational study. Physical Review B, 2010, 81, .	3.2	22
95	Adsorption structure of cyclopentene on<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:mtext>InP</mml:mtext><mml:mrow><mml:mo>(</mml:mo><mml:mrow><mml:mn>001</mml:mn></mml:mrow> Physical Review B, 2009, 80, .	3.2	9
96	Structure of Si(111)-In Nanowires Determined from the Midinfrared Optical Response. Physical Review Letters, 2009, 102, 226805.	7.8	46
97	Analysis of polarizationâ€dependent photoreflectance studies for c â€plane GaN films grown on a â€plane sapphire. Physica Status Solidi (A) Applications and Materials Science, 2009, 206, 773-779.	1.8	4
98	Ellipsometric study of electronic excitations in triglycine sulphate and triglycine selenate crystals. Physica Status Solidi (B): Basic Research, 2009, 246, 2337-2340.	1.5	3
99	Adsorption configurations of hydrocarbon ring molecules on GaAs(001)â€(4 Ã— 4). Physica Status Solidi (B): Basic Research, 2009, 246, 1504-1509.	1.5	9
100	Identification of van Hove singularities in the GaN dielectric function: a comparison of the cubic and hexagonal phase. Physica Status Solidi (B): Basic Research, 2009, 246, 1440-1449.	1.5	48
101	Preface: Phys. Status Solidi B 246/7. Physica Status Solidi (B): Basic Research, 2009, 246, 1413-1414.	1.5	0
102	Influence of anisotropic strain on excitonic transitions in a-plane GaN films. Microelectronics Journal, 2009, 40, 322-324.	2.0	10
103	Molecular Orientation in Octanedithiol and Hexadecanethiol Monolayers on GaAs and Au Measured by Infrared Spectroscopic Ellipsometry. Langmuir, 2009, 25, 919-923.	3.5	37
104	Dielectric function of zinc-blende AlN from 1 to 20 eV: Band gap and van Hove singularities. Journal of Applied Physics, 2009, 106, 076104.	2.5	54
105	Using reflectance anisotropy spectroscopy to characterize capped silver nanostructures grown on silicon. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 2556-2560.	0.8	6
106	Structural and Optical Properties of DNA Layers Covalently Attached to Diamond Surfaces. Langmuir, 2008, 24, 7269-7277.	3.5	38
107	Optical polarizer integrated with suppression of higher harmonics in the vacuum ultraviolet and soft x-ray spectral regions. Applied Physics Letters, 2008, 92, 011110.	3.3	7
108	Spirobifluorene molecular films investigated by means of near infrared-vacuum ultraviolet spectroscopic ellipsometry. Journal of Applied Physics, 2008, 103, 043503.	2.5	0

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109	Ultrathin responsive polyelectrolyte brushes studied by infrared synchrotron mapping ellipsometry. Applied Physics Letters, 2008, 92, .	3.3	20
110	GaN and InN conduction-band states studied by ellipsometry. Physical Review B, 2008, 77, .	3.2	24
111	Band structure and optical spectra of ferroelectric triglycine sulphate. Phase Transitions, 2007, 80, 31-37.	1.3	6
112	Surface phonons of the<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:mi mathvariant="normal">Si</mml:mi><mml:mrow><mml:mo>(</mml:mo><mml:mn>111</mml:mn><mml:mo>)</mml:mo></mml:mrow><mml:mo>−</mml:mo><mml:mi mathvariant="normal">In</mml:mi><mml:mtext>â^’</mml:mtext><mml:mrow><mml:mo>(</mml:mo><mml:mn>4</mml:mn><mml:mo xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inlin. Physical Review B, 2007, 76, .	3.2	28
113	Tunable thin film polarizer for the vacuum ultraviolet and soft x-ray spectral regions. Journal of Applied Physics, 2007, 101, 053114.	2.5	8
114	Dielectric function and Van Hove singularities for In-richInxGa1â^’xNalloys: Comparison of N- and metal-face materials. Physical Review B, 2007, 75, .	3.2	56
115	In Situ Infrared Ellipsometric Study of Stimuli-Responsive Mixed Polyelectrolyte Brushes. Analytical Chemistry, 2007, 79, 7676-7682.	6.5	54
116	Analysis of biosensors by chemically specific optical techniques. Chemiluminescence-imaging and infrared spectroscopic mapping ellipsometry. Analytical and Bioanalytical Chemistry, 2007, 387, 1823-1829.	3.7	23
117	Optical anisotropy of cyclopentene terminated GaAs(001) surfaces. Applied Physics A: Materials Science and Processing, 2007, 87, 469-473.	2.3	10
118	Detailed analysis of the dielectric function for wurtzite InN and In-rich InAlN alloys. Physica Status Solidi (A) Applications and Materials Science, 2006, 203, 42-49.	1.8	53
119	Transition energies and Stokes shift analysis for In-rich InGaN alloys. Physica Status Solidi (B): Basic Research, 2006, 243, 1572-1576.	1.5	6
120	Microfocus-infrared synchrotron ellipsometer for mapping of ultra thin films. Infrared Physics and Technology, 2006, 49, 74-77.	2.9	13
121	Critical points of the band structure and valence band ordering at the point of wurtzite InN. Journal of Crystal Growth, 2006, 288, 273-277.	1.5	38
122	Band structure and UV optical spectra of TGS crystals in the range of 4â€“10eV. Physica B: Condensed Matter, 2006, 373, 328-333.	2.7	19
123	Optical anisotropy and magneto-optical properties of Ni on preoxidizedCu(110). Physical Review B, 2006, 73, .	3.2	34
124	Free-electron response in reflectance anisotropy spectra. Physical Review B, 2006, 74, .	3.2	8
125	Spectroscopic ellipsometry and reflectance anisotropy spectroscopy of biomolecular layers on silicon surfaces. Physica Status Solidi (B): Basic Research, 2005, 242, 2671-2680.	1.5	11
126	Detection of surface states anisotropies at GaAs(001)(2 Ã— 4) decapped surfaces. Physica Status Solidi (B): Basic Research, 2005, 242, 2664-2670.	1.5	1

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127	Structural properties of chalcopyrite thin films studied by Raman spectroscopy. Physica Status Solidi (B): Basic Research, 2005, 242, 2633-2643.	1.5	82
128	Ellipsometry from infrared to vacuum ultraviolet: Structural properties of thin anisotropic guanine films on silicon. Physica Status Solidi (B): Basic Research, 2005, 242, 2681-2687.	1.5	41
129	Optical properties of indium nanowires - an adsorption study. Physica Status Solidi (B): Basic Research, 2005, 242, 2655-2663.	1.5	6
130	MOVPE growth and surface reconstructions of GaAsN(001) surfaces. Physica Status Solidi (B): Basic Research, 2005, 242, 2575-2580.	1.5	1
131	Dielectric function and critical points of the band structure for AlGaN alloys. Physica Status Solidi (B): Basic Research, 2005, 242, 2610-2616.	1.5	38
132	VUV-ellipsometry on GaN: Probing conduction band properties by core level excitations. Physica Status Solidi (B): Basic Research, 2005, 242, 2601-2609.	1.5	11
133	Dielectric functions of DNA base films from near-infrared to ultra-violet. Physica Status Solidi (B): Basic Research, 2005, 242, 3047-3052.	1.5	33
134	Preface: phys. stat. sol. (b) 242/13. Physica Status Solidi (B): Basic Research, 2005, 242, 2548-2549.	1.5	0
135	Molecule-solid interfaces studied with infrared ellipsometry: Ultrathin nitrobenzene films. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2005, 23, 1838.	1.6	26
136	Surface states and resonances on Al(110): Ultraviolet photoemission spectroscopy andab initiocalculations. Physical Review B, 2005, 72, .	3.2	6
137	Analysis of Organic Films and Interfacial Layers by Infrared Spectroscopic Ellipsometry. Applied Spectroscopy, 2005, 59, 272A-282A.	2.2	80
138	Oxidation- and organic-molecule-induced changes of the Si surface optical anisotropy:ab initiopredictions. Journal of Physics Condensed Matter, 2004, 16, S4323-S4334.	1.8	13
139	Optical reflectance anisotropy of Al(110): Experiment andab initiocalculation. Physical Review B, 2004, 69, .	3.2	9
140	Vacuum ultraviolet spectroscopic ellipsometry investigations of guanine layers on H-passivated Si(111) surfaces. Thin Solid Films, 2004, 455-456, 505-508.	1.8	3
141	Anisotropy of the dielectric function for wurtzite InN. Superlattices and Microstructures, 2004, 36, 591-597.	3.1	60
142	Atomic indium nanowires on Si(111): the (4 Ã— 1)â€“(8 Ã— 2) phase transition studied with reflectance anisotropy spectroscopy. Applied Surface Science, 2004, 234, 302-306.	6.1	15
143	Micro-Raman Study of Orientation Effects of CuxSe-Crystallites on Cu-rich CuGaSe2 Thin Films. Journal of Applied Physics, 2004, 96, 1963-1966.	2.5	42
144	In-situ Raman Spectroscopy on IIIâ€“V semiconductors at high temperature in MOVPE. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 2949-2955.	0.8	4

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